

CBCS SCHEME

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17EC33

Third Semester B.E. Degree Examination, Jan./Feb. 2021 Analog Electronics

Time: 3 hrs.

Max. Marks: 100

Note: Answer any FIVE full questions, choosing ONE full question from each module.

Module-1

- 1 a. What is BJT transistor modeling? Obtain the expression for voltage gain, Z_{in} and Z_o of CB configuration using AC equivalent circuit with r_e model. (05 Marks)
- b. Derive the expression for A_v , Z_i and Z_o for a voltage divider bias circuit of BJT, with unbypassed R_E , using r_e equivalent model of BJT. Show the phase relationship between input and output wave form. (10 Marks)
- c. State the characteristic features of Darlington connection. Calculate the DC bias voltages and currents in the circuit.

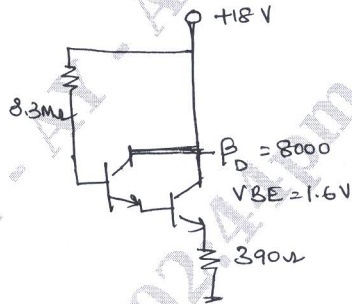


Fig.Q1(c)

(05 Marks)

OR

- 2 a. Give the relation between r_e parameters and h parameters. What are the advantages of h parameters? (05 Marks)
- b. Derive the expressions for current gain, voltage gain, input impedance and output impedance for an emitter follower circuit using approximate hybrid equivalent circuit. (Without the effect of r_o). (10 Marks)
- c. For the network shown in Fig.Q2(c), determine r_e , Z_i , Z_o , A_v (with $r_o = \infty\Omega$) and A_v (with $r_o = 50 K\Omega$)

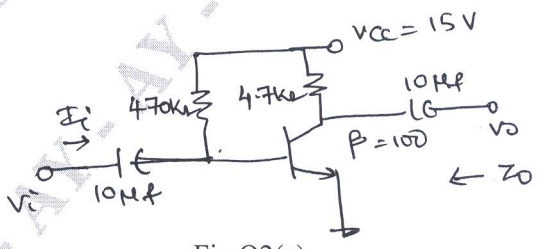


Fig.Q2(c)

(05 Marks)

Module-2

- 3 a. Explain the construction of N channel JFET. Also explain the drain and transfer characteristics of the JFET. (06 Marks)
- b. With equivalent circuit obtain the expression for Z_o and A_v for JFET self bias configuration. (08 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.
2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8 = 50, will be treated as malpractice.

- c. The fixed bias configuration shown in Fig.Q3(c) has $V_{GSQ} = -2V$, $I_{DQ} = 5.625 \text{ mA}$ with $I_{DSS} = 10 \text{ mA}$, $V_P = -8V$ and $Y_{OS} = 40 \mu S$. Determine g_m , r_d , Z_o and A_v .

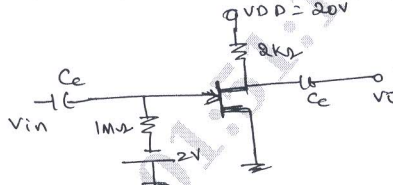


Fig.Q3(c)

(06 Marks)

OR

- 4 a. Differentiate between enhancement and depletion MOSFET. (05 Marks)
 b. With necessary equivalent circuit, obtain the expression for A_v for a JFET source follower configuration. (05 Marks)
 c. Calculate the DC bias, voltage gain, input impedance and output impedance and resulting output voltage for the cascade amplifier shown in Fig.Q4(c). Calculate the load voltage if a 10 KΩ load is connected across the output.

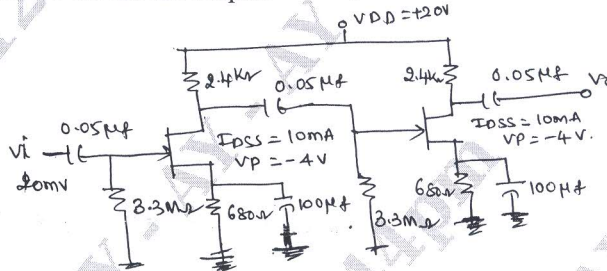


Fig.Q4(c)

(10 Marks)

Module-3

- 5 a. Determine the lower cutoff frequency f_{LS} for the voltage divider bias network using the following parameters:
 $C_S = 10 \mu f$, $C_E = 20 \mu f$, $C_C = 1 \mu f$, $R_S = 1 \text{ K}\Omega$, $R_1 = 40 \text{ K}\Omega$, $R_2 = 10 \text{ K}\Omega$, $R_E = 2 \text{ K}\Omega$, $R_C = 4 \text{ K}\Omega$, $R_L = 2.2 \text{ K}\Omega$, $\beta = 100$, $r_o = \infty \Omega$, $V_{CC} = 20 \text{ V}$, $r_e = 15.76 \Omega$. (04 Marks)
 b. Explain the following: (i) Logarithm (ii) Decibel. With respect to transistor amplifier calculate the overall lower 3 dB and upper 3 dB frequencies for a 3 stage amplifier having an individual $f_1 = 40 \text{ Hz}$ and $f_2 = 2 \text{ MHz}$. (06 Marks)
 c. Discuss the low frequency response of BJT amplifier and give expression for lower cut off frequency due to C_C , C_E and C_S . (10 Marks)

OR

- 6 a. Draw the Hybrid π model for the transistor in CE configuration and explain the significance of each component. (06 Marks)
 b. Describe the Miller effect and derive an equation for Miller input capacitance. (06 Marks)
 c. Determine the high cutoff frequencies for the network shown in Fig.Q6(c).

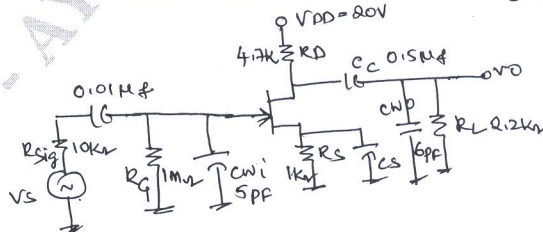


Fig.Q6(c)

(08 Marks)

Module-4

- 7 a. With a block diagram, explain the concept of feedback amplifier and derive the expression for $A_f = \frac{A}{1 + A\beta}$. (06 Marks)
- b. Derive the expression for Z_{if} and Z_{of} for current series feedback amplifier. (08 Marks)
- c. Explain a practical voltage series feedback circuit. (06 Marks)

OR

- 8 a. What is an oscillator? Discuss the concept of generating oscillations with the help of Barkhausen criteria. (05 Marks)
- b. With a neat circuit diagram and necessary expressions, explain the Wein bridge oscillator. (10 Marks)
- c. Design a unijunction transistor for a operation at 1 kHz and 150 kHz assuming $\eta = 0.58$. (05 Marks)

Module-5

- 9 a. Give the definition of power amplifiers and list the types of power amplifiers based on the location of Q point. (05 Marks)
- b. Explain the working of class B complementary symmetry class B push pull amplifier. Obtain an expression for maximum conversion efficiency of this amplifier. (10 Marks)
- c. Calculate the harmonic distortion components for an output signal having fundamental amplitude of 2.5 V, second harmonic amplitude of 0.25 V, third harmonic amplitude of 0.1 V and fourth harmonic amplitude of 0.05 V and also calculate the total harmonic distortion for the amplitude components given above. (05 Marks)

OR

- 10 a. With necessary circuit diagram and characteristic curve, explain the class-A transformer coupled amplifier. Show that the maximum efficiency can be expressed as 50%. (10 Marks)
- b. Describe the block diagram of series and shunt type voltage regulators. (05 Marks)
- c. Calculate the output voltage and Zener current in the regulator circuit of Fig.Q10(c) for $R_L = 5\text{ K}\Omega$.

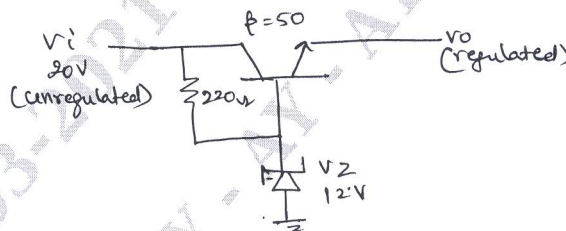


Fig.Q10(c)

(05 Marks)
